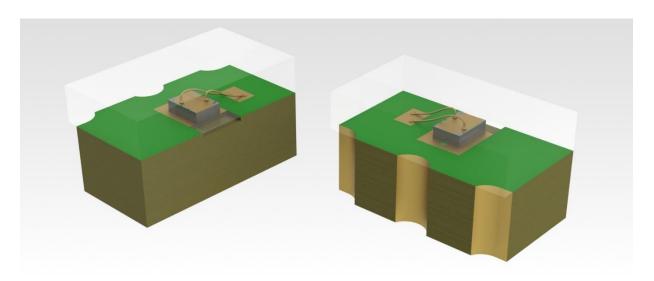
High Power Laser-Diode Family for Commercial Range Finding



Excelitas' pulsed laser diodes produce very high peak optical pulses centered at a wavelength of 905 nm. The package can emit light parallel or perpendicular to the mounting plane.

Key Features

- High Volume Reflow SMD package
- Multi-epi quantum well structure
- Excellent power stability with temperature
- Horizontal and vertical emission possibility
- 75 μm and 225 μm active laser length
- RoHS compliant

Applications

- LiDAR / ToF measurements
- Laser Range Finding
- Laser Scanning / UGV
- Infrared Night Illumination
- Laser Therapy
- Material excitation in medical and other analytical applications

All specifications are valid for $T_A = 23$ °C, $t_p = 100$ ns and $f_p = 1$ kHz, unless otherwise specified.

Table 1: Key parameters

Parameter		Symbol	Minimum	Typical	Maximum	Unit	
Dook Ontical Dower	75 μm, 10 A	P ₇₅	18	20		W	
Peak Optical Power	225 μm, 30 A	P ₂₂₅	65	70			
Wavelength		λς	895	905	925	nm	
Operating Temperature ¹		T _{op}	-40		85	°C	

Note 1: Extended temperature range specification available. Please contact Excelitas Technologies for more information.



High Power Laser-Diode Family for Commercial Range Finding

Table 2: Ordering Information

Parameter	Symbol	TPGAD1S03H	TPGAD1S09H	Unit
Number of stripes	S	3	3	-
Active Area Size	Α	75x10	225x10	μm²
Emitting width ^{1,2}	W	86	263	μm
Emitting height ^{1,2}	h	1	μm	

Note 1: The emitting area is defined as $FWHM(w) \times FWHM(h)$ of the nearfield size at i_F .

Note 2: Parameter depending on drive current. Please contact Excelitas Technologies for more information.

Table 3: Absolute Maximum Ratings

Parameter	Symbol	Value	Units
Peak Reverse Voltage	V_{RM}	2	V
Pulse Duration	t _W	100	ns
Duty Factor	du	0.1	%
Storage Temperature	Ts	-40 1 05	°C

Note 1: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device.

Note 2: Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 4: Emission Specifications

Parameter	Symbol	Minimum	Typical	Maximum	Units
Spectral Width (FWHM)	Δλ		10		nm
Wavelength junction Temperature Coefficient	$\Delta \lambda / \Delta T_j$		0.25		nm/°C
Package Thermal Resistance ¹	R_{th}		70		°C/W
Divergence Parallel to Junction Plane	θΠ		7.5		o
Divergence Perpendicular to Junction Plane	$\theta_{ m L}$		25		o

Note 1: Simulated from the Chip Junction to the cathode PCB connection pad.

High Power Laser-Diode Family for Commercial Range Finding

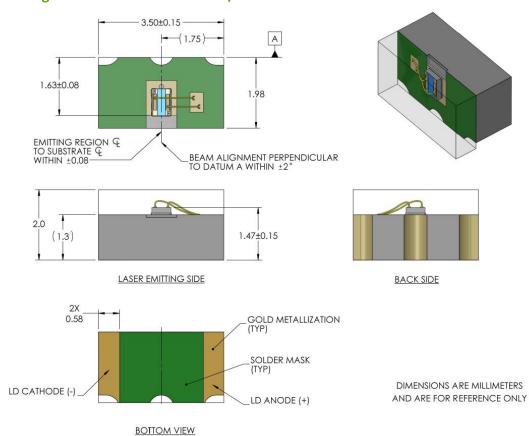
Table 5: Electrical Specifications

		TPGAD1S03H		TPGAD1S09H				
Parameter	Symbol	Minimum	Typical	Maximum	Minimum	Typical	Maximum	Unit
Peak Optical Power ¹	Р	18	20		65	70		W
Drive Current	İF		10			30		Α
Forward Voltage ²	V_{F}		11			13.5		V
Threshold Current	İ _{Th}		0.75			1.75		Α
Series Resistance	R_S		0.454			0.23		Ω
Bandgap Voltage	M		C F			6.5		V
Drop	Vg		6.5			6.5		V
Package Inductance	L _P		1.6			1.6		nH

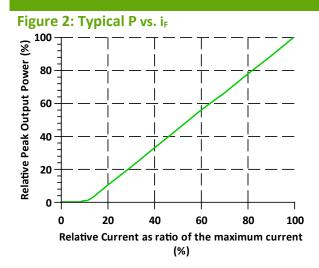
Note 1: at i_F

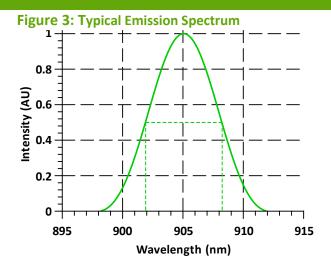
Note 2: As estimated by $V_F = R_S i_F + V_a$.

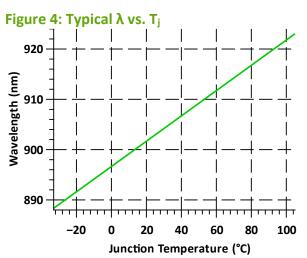
Figure 1: Laser Package Dimension TPGAD1S03H / TPGAD1S09H

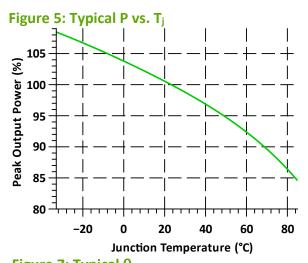


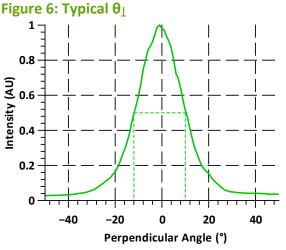
High Power Laser-Diode Family for Commercial Range Finding

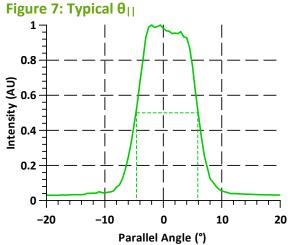












High Power Laser-Diode Family for Commercial Range Finding

Information

Excelitas Technologies' pulsed semiconductor laser, emitting at 905nm in the near IR, uses a multi-layer monolithic chip design. The laser diode is mounted on an FR4 substrate leadless laminate carrier (LLC) with excellent thermal management. This is intended for both surface mount applications and hybrid integration. The encapsulate material is an epoxy resin for low cost and high-volume manufacturing.

The package design and assembly processing techniques are such that the die positioning is well controlled to the reference surfaces. This aids in the alignment of optical elements to the package and is superior to many of the commercially available plastic lead frame TO-18 and SMD style packages in the market.

The SMD package can be mounted with laser beam propagation horizontally or vertically to the PCB surface.

The beam propagation possesses a 25° divergence in the direction perpendicular to the chip surface and 7.5° divergence parallel to the chip surface. The output power shows an excellent stability over the full MIL specification temperature range.

Our quantum well laser design offers rise and fall times of < 1 ns. However, the drive circuit layout and mounting inductance play a dominant role and should be designed in accordance with the desired optical pulse width.

The peak wavelength at 905 nm is centered near the maximum responsivity of most silicon photodiodes. The laser wavelength matches especially well with devices from the Excelitas EPI-APD C30737 family.

The devices are ideally suited for applications where cost is a primary concern and high-volume production capacity is required.

Unconnected laser dies as shipped cannot emit light. Light emission requires an installation into an electrical driver circuit.

High Power Laser-Diode Family for Commercial Range Finding

Principle of operation

The light output of a laser diode is proportional to the current running through the laser by pulsing it in the forward bias direction. A simple way of allowing a large current to flow within nanoseconds through the laser is to discharge a large capacitor into the laser by closing a GaN-FET.

Excelitas recommends the usage of a low-side driver to operate the laser. A detailed description of the circuitry to recharge the capacitors is omitted here since many options are available on the market. The voltage on the capacitors and discharge time will dictate the current flow in the laser.

Electrical circuits should be designed to protect the diodes from high current and reverse voltage transients.

Optimum long-term reliability will be attained with the semiconductor at or below room temperature. Adequate heat sinking should be employed, particularly when operated at maximum duty cycle.

Package inductance

When narrow pulse widths are required, the system designer must take care that circuit inductance is kept to a minimum. Using a low inductance package will reduce the peak voltage required to obtain the desired drive current.

For example, to obtain approximate Gaussian pulse shapes of 40 ns and 1 ns, the below voltage should be considered in addition to the typical forward voltage:

• 40 ns:

o
$$t_p = 40 \text{ ns}, t_r = 20 \text{ ns}$$

o $I_F = 30 \text{ A}, L_P = 1.6 \text{ nH}$
o $V_P = \frac{1.6 \text{ nH} \times 30 \text{ A}}{20 \text{ns}} = 2.4 \text{ V}$

• 1 ns:

o
$$t_p = 1 \text{ ns}, t_r = 0.5 \text{ ns}$$

o $I_F = 30 \text{ A}, L_P = 1.6 \text{ nH}$
o $V_P = \frac{1.6 \text{ nH x } 30 \text{ A}}{0.5 \text{ns}} = 96 \text{ V}$

High Power Laser-Diode Family for Commercial Range Finding

Testing methods

Excelitas verifies the electro optical specifications on every shipped unit.

Visual inspection during fabrication is performed as per our standard and failed lasers are removed.

Packaging and shipping

For sampling quantities, lasers are placed in Waffle Packs.

For production quantities, lasers are placed in Tape & Reel, according to Figure 8.

Orientation (vertical or horizontal) needs to be specified upon order in T&R.

MSL Rating

This series of laser diodes comply with a Moisture Sensitivity Level (MSL) rating of 3 as defined in IPC/JEDEC-J-STD-033C. This allows for up to 168 hour floor life at \leq 30°C / 60%RH once removed from the sealed reel packaging. For complete details refer to the IPC/JEDEC- J-STD-033C specification.

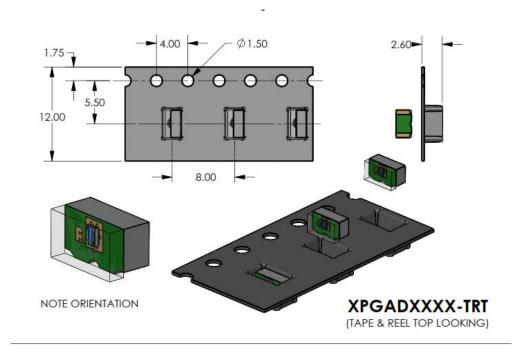
Storage and handling

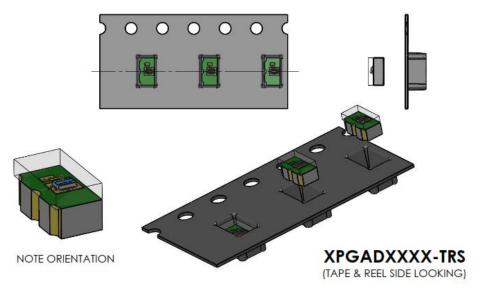
This laser is a static-sensitive device. Therefore, Excelitas highly recommends following the below notes:

- Keep unused devices in ESD-safe material
- Protect devices from static discharge and static fields
- Keep Reels inside their moisture barrier bags until assembly. Respect the MSL rating.
- If a manual picking method is necessary, use a non-marring tweezer to pick the laser by the short sides only.
- Precautions should be taken to avoid reverse polarity of power supply. Reversed polarity of power supply above the breakdown voltage listed under "Absolute Maximum Ratings" results in a destroyed unit.

High Power Laser-Diode Family for Commercial Range Finding

Figure 8: Tape and Reel Packaging Dimensions





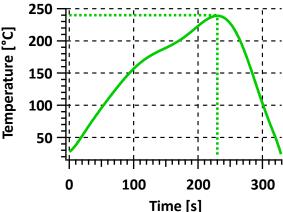
DIMENSIONS ARE MILLIMETERS AND ARE FOR REFERENCE ONLY VS-425R2

High Power Laser-Diode Family for Commercial Range Finding

Table 6: Reflow Solder Profile

The following reflow solder profile is a typical used profile for SAC305 solder alloys. Specific solder parameters depend on the solder alloy used.

Profile Feature	Symbol	Typical	Units
Minimum Sparkling Temperature	T_{Smin}	150	°C
Maximum Sparkling Temperature	T_{Smax}	200	°C
Sparkling Time	ts	75	S
Minimum Reflow Temperature	T_L	217	°C
Peak Temperature	T_P	244	°C
Reflow Time	t_{L}	65	S
Time within T _P - 5°C	t_{P}	25	S
Ramp Down Rate	ΔT_c	2	°C/s



For Your Safety: Laser Radiation

Under operation, these devices produce invisible electromagnetic radiation that may be harmful to the human eye. To ensure that these laser components meet the requirements of Class IIIb laser products, they must not be operated outside their maximum ratings. Power supplies used with these components must be such that the maximum peak forward current cannot be exceeded. It is the responsibility of the user incorporating a laser into a system to certify the Class of use and ensure that it meets the requirements of the ANSI or appropriate authority.

Further details may be obtained in the following publications:

21CFR 1040.10 - "Performance Standards for Light Emitting Products (Laser Products)"

ANSI Z136.1 - "American National Standard for Safe use of Lasers"

IEC 60825-1 - "Safety of Laser Products"

High Power Laser-Diode Family for Commercial Range Finding

RoHS Compliance

This series of APD diodes are designed and built to be fully compliant with the European Union Directive on restrictions of the use of certain hazardous substances in electrical and electronic equipment.



Warranty

A standard 12-month warranty following shipment applies.

About Excelitas Technologies

Excelitas Technologies is a global technology leader focused on delivering innovative, customized solutions to meet the lighting, detection and other high-performance technology needs of OEM customers.

Excelitas has a long and rich history of serving our OEM customer base with optoelectronic sensors and modules for more than 45 years beginning with PerkinElmer, EG&G, and RCA. The constant throughout has been our innovation and commitment to delivering the highest quality solutions to our customers worldwide.

From aerospace and defense to analytical instrumentation, clinical diagnostics, medical, industrial, and safety and security applications, Excelitas Technologies is committed to enabling our customers' success in their specialty end-markets. Excelitas Technologies has approximately 7,000 employees in North America, Europe and Asia, serving customers across the world.

Excelitas Technologies

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